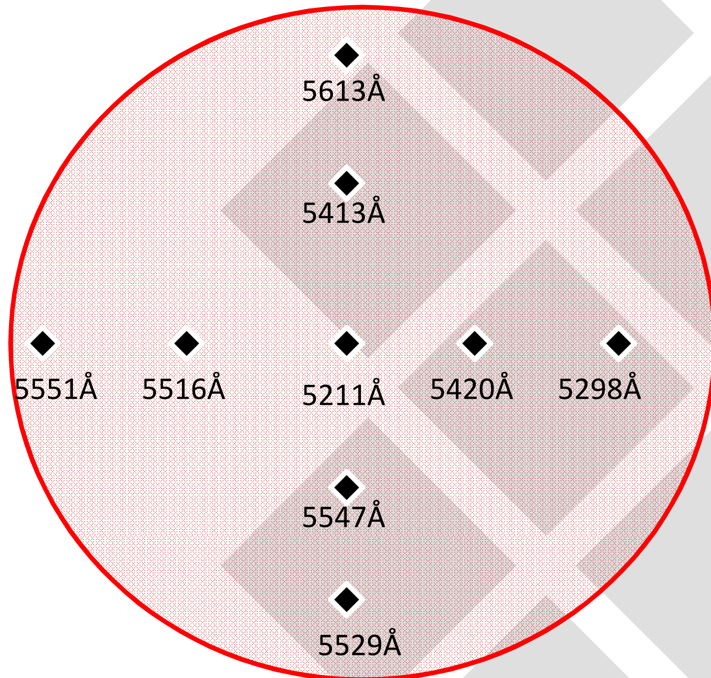
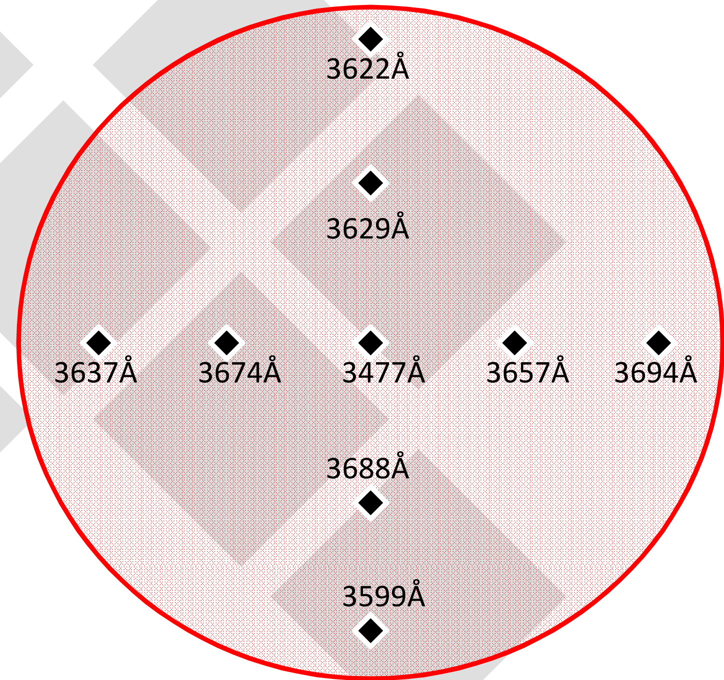
Silicon Dioxide & Silicon Nitride



Parameter used for depositing SiO_2 using PECVD.

Wafer Size	= 6 ”
SiH_4 (sccm)	= 5
Ar(sccm)	= 100
Ar (ring)	= 100
N2O	= 100
Tc (°C)	= 200°C
Time (min)	= 15min
RF Power	= 20W
Pressure	= 0.3T
Uniformity %	= 3.6%
Refractive Index	= 1.48



Parameter used for depositing Si_3N_4 using PECVD.

Wafer Size	= 6 ”
SiH_4 (sccm)	= 5
Ar(sccm)	= 100
Ar (sccm)	= 100
NH3	= 60
Plate Temp (°C)	= 230°C
Time (min)	= 15 min
RF Power	= 30W
Pressure	= 0.3T
Uniformity%	= 2.9%
Refractive Index	= 2.03

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